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26. (amended) The capacitor of claim 23, wherein said annealed top conducting layer is a plasma enhanced annealed top conducting layer.

C<sup>2</sup>

27. (amended) The capacitor of claim 23, wherein said annealed top conducting layer is a remote plasma enhanced annealed top conducting layer.

28. (amended) The capacitor of claim 23, wherein said annealed top conducting layer is an ultraviolet light enhanced annealed top conducting layer.

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98. (twice amended) A capacitor for a semiconductor device, said capacitor comprising:

C<sup>3</sup>

a bottom conducting layer;

an annealed dielectric layer formed over said bottom conducting layer; and

an annealed top conducting layer formed over said annealed dielectric layer, said top conducting layer comprising a metal oxide permeable to oxygen, wherein each of said bottom and annealed top conducting layers is formed of a material selected from the group consisting of platinum, platinum rhodium, platinum iridium, and tungsten nitride.

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